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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

ROBERT H. HAVEMANN ET AL.

Serial No. 09/216,214 (TI-21570)

Filed December 18, 1998

For: ENHANCEMENT TO POLYSILICON GATE

Art Unit 2811

Examiner T. Tran

Commissioner for Patents
Washington, D. C. 20231

Sir:



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TC 2800 MAIL ROOM

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AMENDMENT UNDER 37 C.F.R. 1.116

In response to the Office action dated October 24, 2000, please amend the above identified application as follows:

In the claims:

Amend claim 8 as follows:

8. (Five Times Amended) A transistor structure, comprising:

- G1
- (a) a gate dielectric over a semiconductor region;
 - (b) a patterned gate over said gate dielectric having sidewalls, a top surface remote from [s] said gate dielectric and a bottom surface disposed on said gate dielectric;
 - (c) a lateral growth on said gate dielectric at the corners of said gate, but not under central regions of said gate, [increasing] the thickness of said gate dielectric continually increasing at the